Zefei Wu

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Bridging the gap between atomically thin semiconductors and metal leads. Nature Communications, 2022, 13, 1777.	12.8	17
2	Strained Epitaxy of Monolayer Transition Metal Dichalcogenides for Wrinkle Arrays. ACS Nano, 2021, 15, 6633-6644.	14.6	37
3	Interaction effects and superconductivity signatures in twisted double-bilayer WSe ₂ . Nanoscale Horizons, 2020, 5, 1309-1316.	8.0	68

Oxide Inhibitor-Assisted Growth of Single-Layer Molybdenum Dichalcogenides (MoX₂, X =) Tj ETQq0 0,0 rgBT /Oyerlock 10

4		14.6	30
5	Multiple Regulation over Growth Direction, Band Structure, and Dimension of Monolayer WS ₂ by a Quartz Substrate. Chemistry of Materials, 2020, 32, 2508-2517.	6.7	21
6	Electrically tunable physical properties of two-dimensional materials. Nano Today, 2019, 27, 99-119.	11.9	35
7	Actuators: Singleâ€Crystalline Vanadium Dioxide Actuators (Adv. Funct. Mater. 20/2019). Advanced Functional Materials, 2019, 29, 1970138.	14.9	0
8	Singleâ€Crystalline Vanadium Dioxide Actuators. Advanced Functional Materials, 2019, 29, 1900527.	14.9	37
9	Oil boundary approach for sublimation enabled camphor mediated graphene transfer. Journal of Colloid and Interface Science, 2019, 546, 11-19.	9.4	13
10	Induced Ising spin-orbit interaction in metallic thin films on monolayer <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>WS</mml:mi><mml:msub><mml:m mathvariant="normal">e<mml:mn>2</mml:mn></mml:m </mml:msub></mml:mrow>. Physical Review B, 2019, 99, .</mml:math 	ⁱⁱ 3.2	8
11	Intrinsic valley Hall transport in atomically thin MoS2. Nature Communications, 2019, 10, 611.	12.8	77
12	Determining Interaction Enhanced Valley Susceptibility in Spin-Valley-Locked MoS ₂ . Nano Letters, 2019, 19, 1736-1742.	9.1	35
13	Investigation of the two-gap superconductivity in a few-layer NbSe2 -graphene heterojunction. Physical Review B, 2018, 97, .	3.2	11
14	Twin Defect Derived Growth of Atomically Thin MoS ₂ Dendrites. ACS Nano, 2018, 12, 635-643.	14.6	92
15	Gate-tunable strong-weak localization transition in few-layer black phosphorus. Nanotechnology, 2018, 29, 035204.	2.6	10
16	Fluctuation-induced tunneling conduction in iodine-doped bilayer graphene. Journal of Applied Physics, 2018, 123, 244302.	2.5	2
17	xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" > < mml:mi > p < /mml:mi > < /mml:math >-Type Few-Layer < mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" > < mml:mrow > < mml:msub > < mml:mi > WSe < /mml:mrow > < mml:mp > 2 < /mm	7.8 l:mn>∢/m	37 ml:msubs
18	Physical Review Letters, 2017, 118, 067702. Shape-Dependent Defect Structures of Monolayer MoS ₂ Crystals Grown by Chemical Vapor Deposition. ACS Applied Materials & Interfaces, 2017, 9, 763-770.	8.0	45

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19	Isolation and Characterization of Few-Layer Manganese Thiophosphite. ACS Nano, 2017, 11, 11330-11336.	14.6	98
20	Ambipolar quantum transport in few-layer black phosphorus. Physical Review B, 2017, 96, .	3.2	26
21	Achieving Ultrahigh Carrier Mobility in Two-Dimensional Hole Gas of Black Phosphorus. Nano Letters, 2016, 16, 7768-7773.	9.1	242
22	A reliable way of mechanical exfoliation of large scale two dimensional materials with high quality. AIP Advances, 2016, 6, .	1.3	53
23	Charge density wave phase transition on the surface of electrostatically doped multilayer graphene. Applied Physics Letters, 2016, 109, .	3.3	4
24	Y-shaped ZnO Nanobelts Driven from Twinned Dislocations. Scientific Reports, 2016, 6, 22494.	3.3	10
25	Probing the electronic states and impurity effects in black phosphorus vertical heterostructures. 2D Materials, 2016, 3, 015012.	4.4	16
26	Negative compressibility in graphene-terminated black phosphorus heterostructures. Physical Review B, 2016, 93, .	3.2	10
27	V2O5-C-SnO2 Hybrid Nanobelts as High Performance Anodes for Lithium-ion Batteries. Scientific Reports, 2016, 6, 33597.	3.3	31
28	Even–odd layer-dependent magnetotransport of high-mobility Q-valley electrons in transition metal disulfides. Nature Communications, 2016, 7, 12955.	12.8	82
29	Universal low-temperature Ohmic contacts for quantum transport in transition metal dichalcogenides. 2D Materials, 2016, 3, 021007.	4.4	102
30	Type-controlled nanodevices based on encapsulated few-layer black phosphorus for quantum transport. 2D Materials, 2016, 3, 031001.	4.4	19
31	A fast transfer-free synthesis of high-quality monolayer graphene on insulating substrates by a simple rapid thermal treatment. Nanoscale, 2016, 8, 2594-2600.	5.6	20
32	Detection of interlayer interaction in few-layer graphene. Physical Review B, 2015, 92, .	3.2	22
33	Probing the electron states and metal-insulator transition mechanisms in molybdenum disulphide vertical heterostructures. Nature Communications, 2015, 6, 6088.	12.8	181
34	Hierarchical ZnO Nanostructures with Blooming Flowers Driven by Screw Dislocations. Scientific Reports, 2015, 5, 8226.	3.3	14
35	Probing Defectâ€Induced Midgap States in MoS ₂ Through Graphene–MoS ₂ Heterostructures. Advanced Materials Interfaces, 2015, 2, 1500064.	3.7	17
36	van der Waals Epitaxial Growth of Atomically Thin Bi ₂ Se ₃ and Thickness-Dependent Topological Phase Transition. Nano Letters, 2015, 15, 2645-2651.	9.1	54

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37	High-quality sandwiched black phosphorus heterostructure and its quantum oscillations. Nature Communications, 2015, 6, 7315.	12.8	423
38	Side-gate modulation effects on high-quality BN-Graphene-BN nanoribbon capacitors. Applied Physics Letters, 2014, 105, .	3.3	7
39	Detection of resonant impurities in graphene by quantum capacitance measurement. Physical Review B, 2014, 89, .	3.2	18
40	Semimetallic-to-metallic transition and mobility enhancement enabled by reversible iodine doping of graphene. Nanoscale, 2014, 6, 13196-13202.	5.6	26
41	Negative compressibility observed in graphene containing resonant impurities. Applied Physics Letters, 2013, 102, .	3.3	9
42	Electron-electron interactions in monolayer graphene quantum capacitors. Nano Research, 2013, 6, 619-626.	10.4	17
43	Charge Transfer: Oxygen-Assisted Charge Transfer Between ZnO Quantum Dots and Graphene (Small) Tj ETQq1	1 0.78431 10.0	4 rgBT /Ove
44	Oxygenâ€Assisted Charge Transfer Between ZnO Quantum Dots and Graphene. Small, 2013, 9, 3031-3036.	10.0	174
45	Modification of electronic properties of top-gated graphene devices by ultrathin yttrium-oxide dielectric layers. Nanoscale, 2013, 5, 1116-1120.	5.6	18
46	Density of States and Its Local Fluctuations Determined by Capacitance of Strongly Disordered Graphene. Scientific Reports, 2013, 3, .	3.3	20
47	Negative Quantum Capacitance Induced by Midgap States in Single-layer Graphene. Scientific Reports, 2013, 3, 2041.	3.3	18
48	Modifying electronic transport properties of graphene by electron beam irradiation. Applied Physics Letters, 2011, 99, 033109.	3.3	31